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# MCS6520 PERIPHERAL ADAPTER

## DESCRIPTION

The MCS6520 Peripheral Adapter is designed to solve a broad range of peripheral control problems in the implementation of microcomputer systems. This device allows a very effective trade-off between software and hardware by providing significant capability and flexibility in a low cost chip. When coupled with the power and speed of the MCS6500 family of microprocessors, the MCS6520 allows implementation of very complex systems at a minimum overall cost.

Control of peripheral devices is handled primarily through two 8-bit bi-directional ports. Each of these lines can be programmed to act as either an input or an output. In addition, four peripheral control/interrupt input lines are provided. These lines can be used to interrupt the processor or for "hand-shaking" data between the processor and a peripheral device.

- High performance replacement for Motorola/AMI/MOSTEK/Hitachi peripheral adapter.
- N channel, depletion load technology, single +5V supply.
- · Completely Static and TTL compatible.
- · CMOS compatible peripheral control lines.
- Fully automatic "hand-shake" allows very positive control of data transfers between processor and peripheral devices.



V <sub>SS</sub> C	1	40	CA1
PAØ 🗖	2	39	CA2
PA1	3	38	IRQA
PA2	4	37	IRQB
PA3	5 6	36 35	RSØ RS1
PA4 C PA5 C	7	33	REST
PAS C PA6 C	8	33	DØ
PA7 C	9	32	D1
PBØ C	10	31	D2
PB1 C	11	30	D3
PB2	12	29	D4
РВЗ 🗖	13	28	D5
PB4 🗲	14	27	D6
PB5 C	15	26	D <b>7</b>
PB6 🗲	16	25	02
РВ7 🗲	17	24	CS1
CB1	18	23	CS2
CB2	19	22	CSØ D/W
V <sub>CC</sub> C	20	21	R/W

# SUMMARY OF MCS6520 OPERATION

See MOS TECHNOLOGY Microcomputer Hardware Manual for detailed description of MCS6520 operation.

CD 4			CA1/CBI CONTROL
<u>CRA</u> Bit 1	(CRB) Bit 0	Active Transition of Input Signal*	IRQA (IRQB) Interrupt Outputs
0	0	negative	Disableremain high
0	1	negative	Enablegoes low when bit 7 in CRA (CRB) is set by active transition of signal on CA1 (CB1)
1	0	positive	Disableremain high
1	1	positive	Enableas explained above

signal. This is independent of the state of Bit 0 in CRA (CRB).

CRA (CRB)		<u>,</u>		IDOA (IDOD)
Bit S	Bit 4	Bit 3	Active Transition of Input Signal*	IRQA (IRQB) Interrupt Output
0	0	0	negative	Disableremains high
0	0	1	negative	Enablegoes low when bit 6 in CRA (CRB) is set by active transition of signal on CA2 (CB2)
0	1	0	positive	Disableremains high
0	1	1	positive	Enableas explained above

\*Note: Bit 6 of CRA (CRB) will be set to a logic 1 by an active transition of the CA2 (CB2) signal. This is independent of the state of Bit 3 in CRA (CRB).

<u>.</u>		CRA		CA	2 OUTPUT MODES
	Bit 5	Bit 4	Bit 3	Mode	Description
5	1	0	0	"Handshake" on Read	CA2 is set high on an active transition of the CA1 interrupt input signal and set low by a microprocessor "Read A Data" operation. This allows positive control of data transfers from the peripheral device to the microprocessor.
	1	0	1	Pulse Output	CA2 goes low for one cycle after a "Read A Data" operation. This pulse can be used to signal the peripheral device that data was taken.
	1	1	0	Manual Output	CA2 set low
	1	1	1	Manual Output	CA2 set high

## **CB2 OUTPUT MODES**

	CRB			
Bit 5	Bit 4	Bit 3	Mode	Description
1	0	0	"Handshake" on Write	CB2 is set low on microprocessor "Write B Data" operation and is set high by an active transition of the CB1 interrupt input signal. This allows positive control of data transfers from the microprocessor to the peripheral device.
1	0	1	Pulse Output	CB2 goes low for one cycle after a microprocessor "Write B Data" operation. This can be used to signal the peripheral device that data is available.
1	1	0	Manual Output	CB2 set low
1	1	1	Manual Output	CB2 set high

MAXIMUM RATINGS				
Rating	Symbol	Value	Unit	
Supply Voltage	V <sub>CC</sub>	-0.3 to +7.0	V <sub>dc</sub>	This device contains circuitry to protect the inputs against
Input Voltage	Vin	-0.3 to +7.0	V <sub>dc</sub>	damage due to high static voltages, however, it is
Operating Temperature Range	T <sub>A</sub>	0 to +70	°C	advised that normal precautions be taken to avoid application
Storage Temperature Range	Tstg	-55 to +150	°C	of any voltage higher than maximum rated voltages to this circuit.

STATIC D.C. CHARACTERISTICS ( $V_{CC}$  = 5.0 V  $\pm$  5%,  $V_{SS}$  = 0,  $T_A$  = 25°C unless otherwise noted)

Characteri	Symbol	Min	Тур	Max	Unit	
Input High Voltage (Normal Operating	V <sub>IH</sub>	+2.0	_	VCC	Vdc	
Input Low Voltage (Normal Operating Levels)			-0.3	-	+.8	Vdc
Input Threshold Voltage	$V_{IL}$ $V_{IT}$	0.8		2.0	Vdc	
Input Leakage Current		IIN				µAdc
$V_{in} = 0$ to 5.0 Vdc		IN	_	+1.0	+2.5	
R/W, Reset, RSØ, RS1, CSØ, C	S1, CS2, CA1, CB1, \$2			_	-	
Three-State (Off State Input Current		ITSI				
$(V_{in} = 0.4 \text{ to } 2.4 \text{ Vdc}, V_{CC} = \text{max})$		151	-	+2.0	+10	µAdc
Input High Current		I <sub>IH</sub>		_	-	
$(V_{\rm IH} = 2.4  \rm Vdc)$	PAØ-PA7.CA2	In	-100	-250	_	µAdc
Input Low Current		IIL				
$(V_{1L} = 0.4 \text{ Vdc})$	PAØ-PA7,CA2	I L	-	-1.0	-1.6	mAdc
Output High Voltage		VOH				
$(V_{CC} = \min, 1_{Load} = -100 \mu Adc)$		011	2.4	1997 <u>-</u> 1997	_	Vdc
Output Low Voltage		VOL				
$(V_{CC} = \min, 1_{Load} = 1.6 \text{ mAdc})$		OL	_	_	+0.4	Vdc
Output High Current (Sourcing)		I <sub>OH</sub>				
$(V_{OH} = 2.4 \text{ Vdc})$		UH	-100	-1000	_	uAdc
$(V_0 = 1.5 \text{ Vdc}, \text{ the current for dri})$	ving other than			-2.5	_	mAdc
TTL, e.g., Darlington Base)						
Output Low Current (Sinking)		IOL				
$(V_{OL} = 0.4 \text{ Vdc})$		-OL	1.6	_	1.1	mAdc
	IRQA, IRQB	Ioff	_	1.0	10	uAdc
Power Dissipation		PD	_	200	500	mW
Input Capacitance		Cin		200	000	pF
$(V_{in} - 0, T_A = 25^{\circ}C, f = 1.0 \text{ MHz})$		om				P.
DØ-D7, PAØ-PA7, PBØ-	PB7 CA2 CB2		_	_	10	
R/W, Reset, RSØ, RS1, C			_	_	7.0	
CA1,CB1, 42	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,		_	_	20	
Output Capacitance		Cout			20	
$(V_{in} - 0, T_A = 25^{\circ}C, f = 1.0 \text{ MHz})$		Cout		_	10	pF
(111 0, 1A = 200, 1 = 1.0 M12)					10	P

NOTE: Negative sign indicates outward current flow, positive indicates inward flow.





#### A.C. CHARACTERISTICS

Read Timing Characteristics (Figure 1, Loading 130 pF and one TTL load)

Characteristics	Symbol	Min	Тур	Max	Unit	
Delay Time, Address valid to Enable positive transition	TAEW	180	_	_	ns	
Delay Time, Enable positive transition to Data valid on bus	TEDR	-	-	395	ns	
Peripheral Data Setup Time	TPDSU	300	-	-	ns	
Data Bus Hold Time	T <sub>HR</sub>	10		-	ns	
Delay Time, Enable negative transition to CA2 negative transition	T <sub>CA2</sub>	-	-	1.0	us	
Delay Time, Enable negative transition to CA2 positive transition	T <sub>RS1</sub>	-	-	1.0	us	
Rise and Fall Time for CA1 and CA2 input signals	tr,tf	-	-	1.0	us	
Delay Time from CA1 active transition to CA2 positive transition	T <sub>RS2</sub>	-	-	2.0	us	
Rise and Fall Time for Enable input	trE,tfE	-	-	25	us	

### Write Timing Characteristics (Figure 2)

Characteristics	Symbol	Min	Тур	Max	Unit	
Enable Pulse Width	TE	0.470	_	25	μs	
Delay Time, Address valid to Enable positive transition	TAEW	180	-	-	ns	
Delay Time, Data valid to Enable negative transition	TDSU	300	-		ns	
Delay Time, Read/Write negative transition to Enable positive transition	TWE	130	-	-	ns	
Data Bus Hold Time	T <sub>HW</sub>	10	-	-	ns	
Delay Time, Enable negative transition to Peripheral Data valid	TPDW	-	-	1.0	us	
Delay Time, Enable negative transition to Peripheral Data Valid, CMOS (V <sub>CC</sub> - 30%) PAØ-PA7, CA2	TCMOS	-	-	2.0	μs	
Delay Time, Enable positive transition to CB2 negative transition	T <sub>CB2</sub>	_	-	1.0	us	
Delay Time, Peripheral Data valid to CB2 negative transition	TDC	0	-	1.5	us	
Delay Time, Enable positive transition to CB2 positive transition		-	-	1.0	us	
Rise and Fall Time for CB1 and CB2 input signals	tr,tf	_	-	1.0	uS	
Delay Time, CB1 active transition to CB2 positive transition	T <sub>RS2</sub>	-	-	2.0	μs	